

MJE340

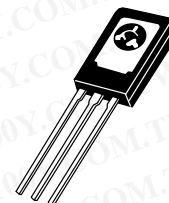
**Plastic Medium Power NPN
Silicon Transistor**

... useful for high-voltage general purpose applications.

- Suitable for Transformerless, Line-Operated Equipment
- Thermopad Construction Provides High Power Dissipation Rating for High Reliability

**0.5 AMPERE
POWER TRANSISTOR
NPN SILICON
300 VOLTS
20 WATTS**

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-54151736
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)



**CASE 77-08
TO-225AA TYPE**

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	300	Vdc
Emitter-Base Voltage	V_{EB}	3.0	Vdc
Collector Current — Continuous	I_C	500	mAdc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	20 0.16	Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θ_{JC}	6.25	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Sustaining Voltage ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	$V_{CEO(sus)}$	300	—	Vdc
Collector Cutoff Current ($V_{CB} = 300 \text{ Vdc}, I_E = 0$)	I_{CBO}	—	100	μAdc
Emitter Cutoff Current ($V_{EB} = 3.0 \text{ Vdc}, I_C = 0$)	I_{EBO}	—	100	μAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 50 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$)	h_{FE}	30	240	—
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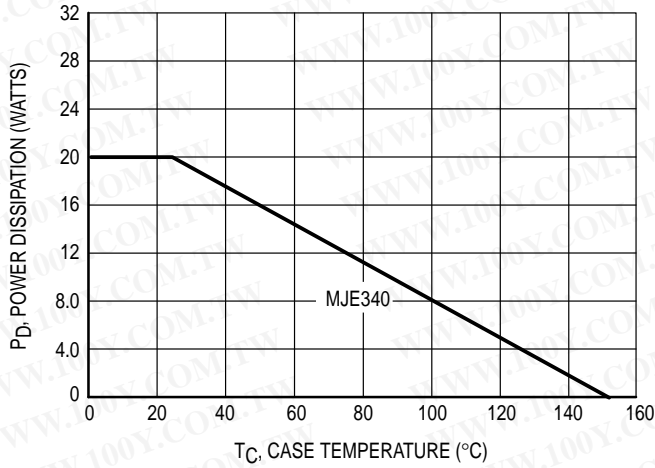


Figure 1. Power Temperature Derating

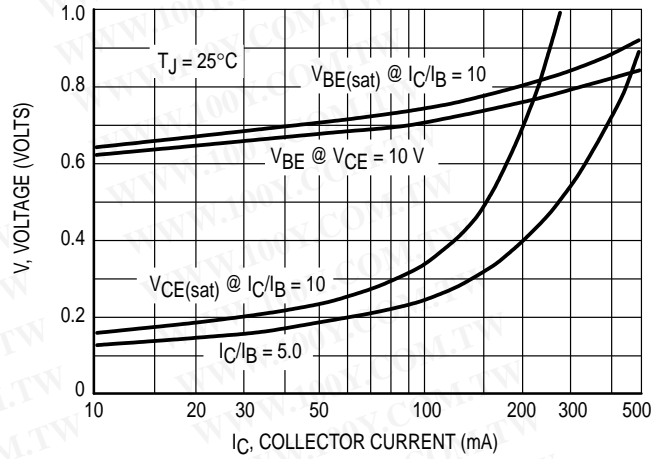


Figure 2. "On" Voltages

ACTIVE-REGION SAFE OPERATING AREA

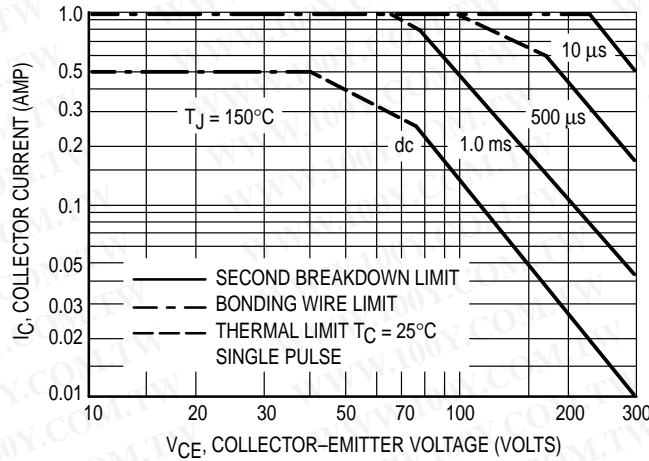


Figure 3. MJE340

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There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 3 is based on $T_{J(pk)} = 150^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150^\circ\text{C}$. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

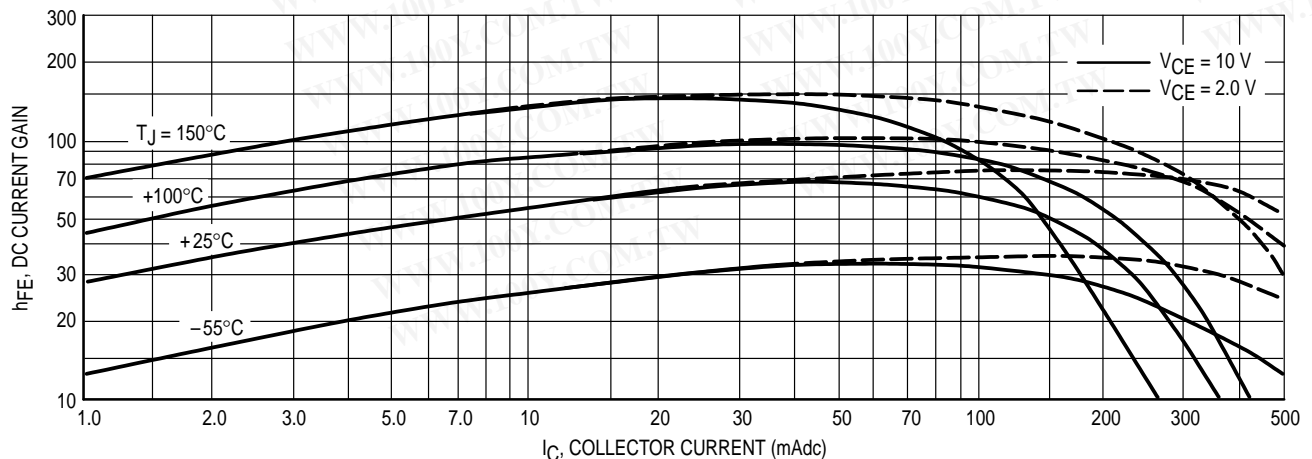
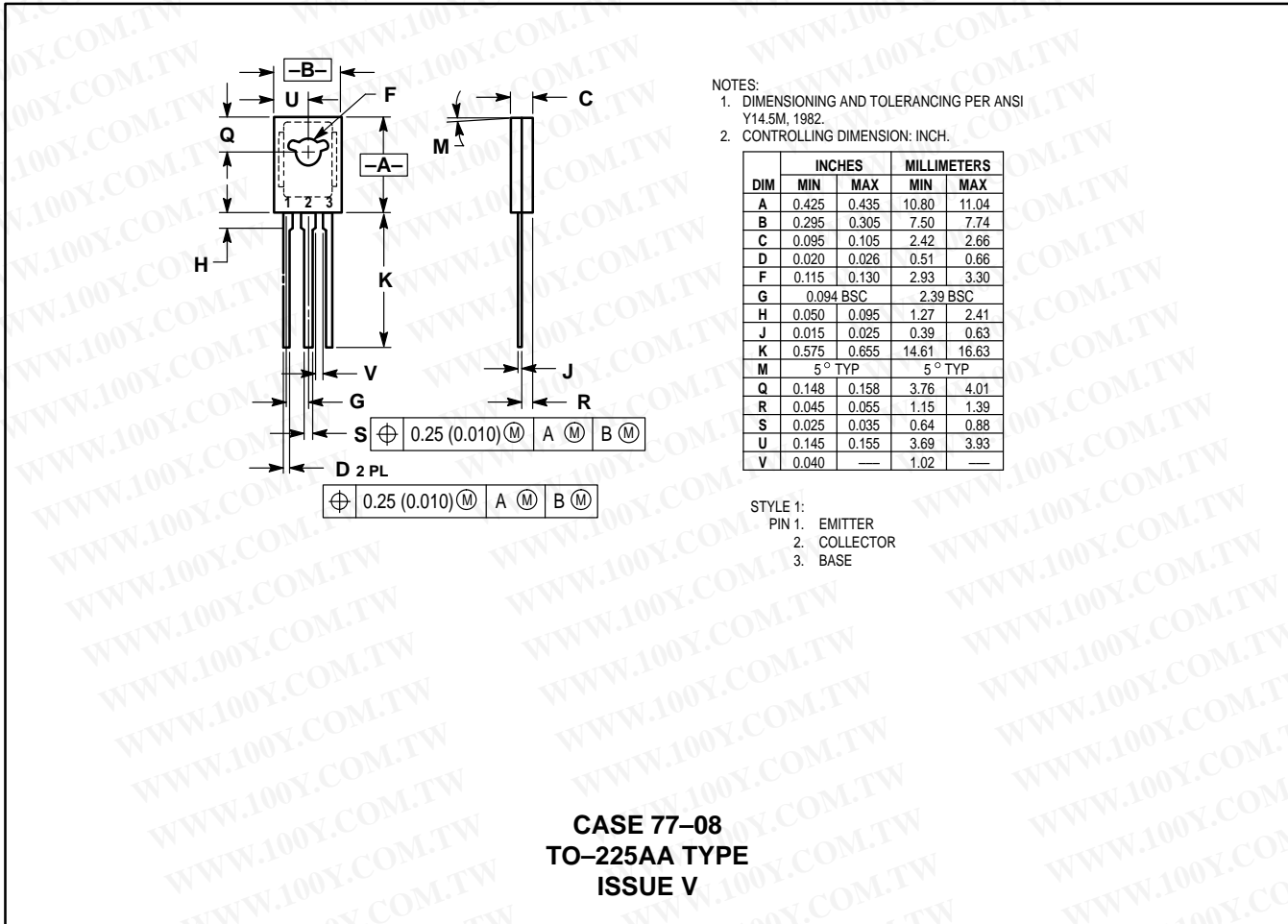


Figure 4. DC Current Gain

PACKAGE DIMENSIONS



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